SN65LVDS122
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# 1.5-Gbps $2 \times 2$ LVDS CROSSPOINT SWITCH 

## FEATURES

- Designed for Signaling Rates ${ }^{(1)}$ Up To 1.5 Gbps
- Total Jitter < 65 ps
- Pin-Compatible With SN65LVDS22 and SN65LVDM22
- 25 mV of Receiver Input Threshold Hysteresis Over 0-V to 4-V Common-Mode Range
- Inputs Electrically Compatible With CML, LVPECL and LVDS Signal Levels
- Propagation Delay Times, 900 ps Maximum
- LVDT Integrates 110- $\Omega$ Terminating Resistor
- Offered in SOIC and TSSOP


## APPLICATIONS

- 10-G (OC-192) Optical Modules
- $\mathbf{6 2 2}-\mathrm{MHz}$ Central Office Clock Distribution
- Wireless Basestations
- Low Jitter Clock Repeater/Multiplexer
- Protection Switching for Serial Backplanes
(1) The signlaing rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).


## DESCRIPTION

The SN65LVDS122 and SN65LVDT122 are crosspoint switches that use low voltage differential signaling (LVDS) to achieve signaling rates as high as 1.5 Gbps. They are pin-compatible speed upgrades to the SN65LVDS22 and SN65LVDM22. The internal signal paths maintain differential signaling for high speeds and low signal skews. These devices have a $0-\mathrm{V}$ to $4-\mathrm{V}$ common-mode input range that accepts LVDS, LVPECL, or CML inputs. Two logic pins (S0 and S1) set the internal configuration between the differential inputs and outputs. This allows the flexibility to perform the following configurations: $2 \times 2$ crosspoint switch, 2:1 input multiplexer, 1:2 splitter or dual repeater/translator within a single device. Additionally, SN65LVDT122 incorporates a $110-\Omega$ termination resistor for those applications where board space is a premium. Although these devices are designed for 1.5 Gbps, some applications at a 2 -Gbps data rate can be supported depending on loading and signal quality.

The intended application of this device is ideal for loopback switching for diagnostic routines, fanout buffering of clock/data distribution provide protection in fault-tolerant systems, clock multiplexing in optical modules, and for overall signal boosting over extended distances.
The SN65LVDS122 and SN65LVDT122 are characterized for operation from $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$.


[^0]These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

| PACKAGE | TERMINATION RESISTOR | PART NUMBER $^{(\mathbf{1})}$ | SYMBOLIZATION |
| :---: | :---: | :---: | :---: |
| SOIC | No | SN65LVDS122D | LVDS122 |
| SOIC | Yes | SN65LVDT122D | LVDT122 |
| TSSOP | No | SN65LVDS122PW | LVDS122 |
| TSSOP | Yes | SN65LVDT122PW | LVDT122 |

(1) Add the suffix R for taped and reeled carrier

## ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted ${ }^{(1)}$

|  |  |  |  | SN65LVDS122, SN65LVDT122 |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Supply voltage range ${ }^{(2)}$ |  |  | -0.5 V to 4 V |
|  | Voltage range | (A, B) |  | -0.7 V to 4.3 V |
|  |  | $\left\|\mathrm{V}_{\mathrm{A}}-\mathrm{V}_{\mathrm{B}}\right\|$ (LVDT only) |  | 1 V |
|  |  | (DE, S0, S1) |  | -0.5 V to 4 V |
|  |  | (Y, Z) |  | -0.5 V to 4 V |
|  | ESD | Human Body Model ${ }^{(3)}$ | A, B, Y, Z, and GND | $\pm 4 \mathrm{kV}$ |
|  |  |  | All pins | $\pm 2 \mathrm{kV}$ |
|  |  | Charged-Device Model ${ }^{(4)}$ | All pins | $\pm 1500 \mathrm{~V}$ |
|  | Continuous power dissipation |  |  | See Dissipation Rating Table |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature range |  |  | $-65^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ |
| Lead temperature $1,6 \mathrm{~mm}(1 / 16 \mathrm{inch})$ from case for 10 seconds | Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds |  |  | $260^{\circ} \mathrm{C}$ |

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.7.
(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

## RECOMMENDED OPERATING CONDITIONS

|  |  |  | MIN | NOM | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Supply voltage |  | 3 | 3.3 | 3.6 | V |
| $\mathrm{V}_{\mathrm{IH}}$ | High-level input voltage | S0, S1, 1DE, 2DE | 2 |  | 4 | V |
|  | Low-level input voltage | S0, S1, 1DE, 2DE | 0 |  | 0.8 | V |
|  | Magnitude of differential input voltage | LVDS | 0.1 |  | 1 |  |
| \|VID |  | LVDT | 0.1 |  | 0.8 |  |
|  | Input voltage (any combination of com | de or input signals) | 0 |  | 4 | V |
|  | Operating free-air temperature |  | -40 |  | 85 | ${ }^{\circ} \mathrm{C}$ |

## PACKAGE DISSIPATION RATINGS

| PACKAGE | $\mathbf{T}_{\mathbf{A}} \leq \mathbf{2 5}{ }^{\circ} \mathbf{C}$ <br> POWER RATING | DERATING FACTOR ${ }^{(1)}$ <br> ABOVE $\mathbf{T}_{\mathbf{A}}=\mathbf{2 5}{ }^{\circ} \mathbf{C}$ | $\mathbf{T}_{\mathbf{A}}=\mathbf{8 5}{ }^{\circ} \mathbf{C}$ <br> POWER RATING |
| :---: | :---: | :---: | :---: |
| PW | 712 mW | $6.2 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 340 mW |
| D | 1002 mW | $8.7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 480 mW |

(1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

## INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

| PARAMETER |  |  | TEST CONDITIONS | MIN | TYP ${ }^{(1)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{1 \mathrm{~T}_{+}}$ | Positive-going differential input voltage threshold |  | See Eiqure_1 and Table 1 |  |  | 100 | mV |
| $\mathrm{V}_{\text {IT }}$ - | Negative-going differential input voltage threshold |  | See Eigure_1 and Table 1 | $-100^{(2)}$ |  |  | mV |
| $\mathrm{V}_{\text {ID(HYS }}$ | Differential input voltage hysteresis ( $\mathrm{V}_{\mathrm{IT}+}-\mathrm{V}_{\mathrm{IT}-}$ ) |  |  |  | 25 |  | mV |
| ${ }^{1} \mathrm{H}$ | High-level input current | DE | $\mathrm{V}_{\mathrm{IH}}=2$ | -10 |  | 0 | $\mu \mathrm{A}$ |
|  |  | S0, S1 |  | 0 |  | 20 |  |
|  | Low-level input current | DE | $\mathrm{V}_{\mathrm{IL}}=0.8 \mathrm{~V}$ | -10 |  | 0 | $\mu \mathrm{A}$ |
|  |  | S0, S1 |  |  |  | 20 |  |
| $\mathrm{I}_{\mathrm{cc}}$ | Supply current |  | $\mathrm{R}_{\mathrm{L}}=100 \Omega$ |  | 80 | 100 | mA |
|  |  |  | Disabled |  | 35 | 45 |  |
| 1 | Input current (A or B inputs 'LVDS) |  | $\mathrm{V}_{1}=0 \mathrm{~V}$ or 2.4 V , Other input at 1.2 V | -20 |  | 20 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{1}=4 \mathrm{~V}$, Other input at 1.2 V | 0 |  | 33 |  |
|  | Input current (A or B inputs 'LVDT) |  | $\mathrm{V}_{1}=0 \mathrm{~V}$ or 2.4 V , Other input open | -40 |  | 40 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{1}=4 \mathrm{~V}$, Other input open | 0 |  | 66 |  |
| $I_{\text {(IOFF) }}$ | Input current (A or B inputs 'LVDS) |  | $\mathrm{V}_{\mathrm{cc}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{I}}=0 \mathrm{~V} \text { or } 2.4 \mathrm{~V}$ <br> Other input at 1.2 V | -20 |  | 20 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{\mathrm{cc}}=1.5 \mathrm{~V}, \mathrm{~V}_{1}=2.4 \mathrm{~V} \text { or } 4 \mathrm{~V} \text {, }$ <br> Other input at 1.2 V | 0 |  | 33 |  |
|  | Input current (A or B inputs 'LVDT) |  | $\mathrm{V}_{\mathrm{cc}}=1.5 \mathrm{~V}, \mathrm{~V}_{1}=0 \mathrm{~V} \text { or } 2.4 \mathrm{~V} \text {, }$ <br> Other input open | -40 |  | 40 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{\mathrm{CC}}=1.5 \mathrm{~V}, \mathrm{~V}_{1}=2.4 \mathrm{~V} \text { or } 4 \mathrm{~V} \text {, }$ <br> Other input open | 0 |  | 66 |  |
| $\mathrm{I}_{10}$ | Input offset current (\| $\\|_{\text {IA }}$ | IIB \|) 'LVDS | $\mathrm{V}_{\mathrm{IA}}=\mathrm{V}_{\mathrm{IB}}, 0 \leq \mathrm{V}_{\mathrm{IA}} \leq 4 \mathrm{~V}$ | -6 |  | 6 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\mathrm{T}}$ | Termination resistance ('LVDT) |  | $\begin{aligned} & \mathrm{V}_{\text {ID }}=300 \mathrm{mV} \text { and } 500 \mathrm{mV}, \\ & \mathrm{~V}_{\text {IC }}=0 \mathrm{~V} \text { to } 2.4 \mathrm{~V} \end{aligned}$ | 90 | 110 | 132 | $\Omega$ |
|  | Termination resistance ('LVDT with power-off) |  | $\begin{aligned} & \mathrm{V}_{\mathrm{ID}}=300 \mathrm{mV} \text { and } 500 \mathrm{mV}, \\ & \mathrm{~V}_{\mathrm{CC}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IC}}=0 \mathrm{~V} \text { to } 2.4 \mathrm{~V} \end{aligned}$ | 90 | 110 | 132 |  |
| $\mathrm{C}_{1}$ | Differential input capacitance ('LVDT with power-off) |  | $\mathrm{V}_{1}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ | 3 |  |  | pF |
|  |  |  | Powered down ( $\mathrm{V}_{\mathrm{CC}}=1.5 \mathrm{~V}$ ) |  | 3 |  |  |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.
(2) The algebraic convention in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

## OUTPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

|  | PARAMETER | TEST CONDITIONS | MIN | TYP(1) | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| \| $\mathrm{V}_{\text {OD }}$ \| | Differential output voltage magnitude | See Eigure2 | 247 | 310 | 454 | mV |
| $\Delta\left\|\mathrm{V}_{\text {OD }}\right\|$ | Change in differential output voltage magnitude between logic states |  | -50 |  | 50 |  |
| $\mathrm{V}_{\mathrm{OC}(\mathrm{SS})}$ | Steady-state common-mode output voltage | See Eigure 3 | 1.125 |  | 1.375 | V |
| $\Delta \mathrm{V}_{\text {OC(SS) }}$ | Change in steady-state common-mode output voltage between logic states |  | -50 |  | 50 | mV |
| $\mathrm{V}_{\text {OC(PP) }}$ | Peak-to-peak common-mode output voltage |  |  | 50 | 150 | mV |
| Ios | Short-circuit output current | $\mathrm{V}_{\mathrm{O}(\mathrm{Y})}$ or $\mathrm{V}_{\mathrm{O}(\mathrm{Z})}=0 \mathrm{~V}$ | -24 |  | 24 | mA |
| $\mathrm{los}(\mathrm{D})$ | Differential short-circuit output current | $\mathrm{V}_{\mathrm{OD}}=0 \mathrm{~V}$ | -12 |  | 12 | mA |
| $\mathrm{l}_{\text {Oz }}$ | High-impedance output current | $\mathrm{V}_{\mathrm{OD}}=600 \mathrm{mV}$ | -1 |  | 1 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{O}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | -1 |  | 1 |  |
| $\mathrm{C}_{0}$ | Differential output capacitance | $\mathrm{V}_{1}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ | 3 |  |  | pF |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply. SN65LVDT122
SLLS525B-MAY 2002-REVISED JUNE 2004
TIMING CHARACTERISTICS

|  | PARAMETER | TEST CONDITIONS | MIN | NOM |
| :--- | :--- | :---: | :---: | :---: |
| $t_{\text {SET }}$ | Input to select setup time |  | 0 |  |
| $t_{\text {HOLD }}$ | Input to select hold time |  | UNIT |  |
| $t_{\text {SWITCH }}$ | Select to switch output |  | 0.5 |  |

## SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

|  | PARAMETER | TEST CONDITIONS | MIN | NOM ${ }^{(1)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {PLH }}$ | Propagation delay time, low-to-high-level output | See Eigure 4 | 400 | 650 | 900 | ps |
| $\mathrm{t}_{\mathrm{PHL}}$ | Propagation delay time, high-to-low-level output |  | 400 | 650 | 900 | ps |
| $\mathrm{t}_{\mathrm{r}}$ | Differential output signal rise time (20\%-80\%) |  |  |  | 280 | ps |
| $\mathrm{t}_{\mathrm{f}}$ | Differential output signal fall time (20\%-80\%) |  |  |  | 280 | ps |
| $\mathrm{t}_{\text {sk(p) }}$ | Pulse skew (\|t $\left.\mathrm{t}_{\text {PHL }}-\mathrm{t}_{\text {PLH }} \mid\right)^{(2)}$ |  |  | 10 | 50 | ps |
| $\mathrm{t}_{\text {sk(pp) }}$ | Part-to-part skew ${ }^{(3)}$ | $\mathrm{V}_{\text {ID }}=0.2 \mathrm{~V}$ |  |  | 100 | ps |
| $\mathrm{t}_{\text {jit(per) }}$ | Period jitter, rms (1 standard deviation) ${ }^{(4)}$ | 750 MHz clock input ${ }^{(5)}$ |  | 1 | 2.2 | ps |
| $\mathrm{t}_{\mathrm{jit}(\mathrm{cc})}$ | Cycle-to-cycle jitter (peak) ${ }^{(4)}$ | 750 MHz clock input( ${ }^{(6)}$ |  | 10 | 17 | ps |
| $\mathrm{t}_{\text {jit(pp) }}$ | Peak-to-peak jitter ${ }^{(4)}$ | 1.5 Gbps $2^{23}-1$ PRBS input ${ }^{(7)}$ |  | 33 | 65 | ps |
| $\mathrm{t}_{\mathrm{jit}}$ (det) | Deterministic jitter, peak-to-peak ${ }^{(4)}$ | 1.5 Gbps $2^{7}-1$ PRBS input ${ }^{(8)}$ |  | 17 | 50 | ps |
| $\mathrm{t}_{\mathrm{PHZ}}$ | Propagation delay time, high-level-to-high-impedance output | See Eigure 5 |  | 6 | 8 | ns |
| $\mathrm{t}_{\text {PLZ }}$ | Propagation delay time, low-level-to-high-impedance output | See Eigure 5 |  | 6 | 8 | ns |
| $\mathrm{t}_{\text {PZH }}$ | Propagation delay time, high-impedance-to-high-level output | See Eigure 5 |  | 4 | 6 | ns |
| $\mathrm{t}_{\text {PZL }}$ | Propagation delay time, high-impedance-to-low-level output | See Eigure 5 |  | 4 | 6 | ns |
| $\mathrm{t}_{\text {sk(0) }}$ | Output skew ${ }^{(9)}$ |  |  | 15 | 40 | ps |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.
(2) $t_{\text {sk(p) }}$ is the magnitude of the time difference between the $t_{P L H}$ and $t_{P H L}$ of any output of a single device.
(3) $t_{\text {sk }(p \mathrm{pp})}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.
(4) Jitter is specified by design and characterization. Stimulus jitter has been subtracted.
(5) Input voltage $=\mathrm{V}_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $750 \mathrm{MHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$, measured over 1000 samples.
(6) Input voltage $=V_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $750 \mathrm{MHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.
(7) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{23}-1$ PRBS pattern at $1.5 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$, measured over 200 k samples.
(8) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{7}-1$ PRBS pattern at $1.5 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.
(9) Output skew is the magnitude of the time delay difference between the outputs of a single device with all inputs tied together.

## PIN ASSIGNMENT

D OR PW PACKAGE (TOP VIEW)

|  | 10 | 16 |  |
| :---: | :---: | :---: | :---: |
| 1B ■ |  |  | $\square \mathrm{V}_{\mathrm{CC}}$ |
| 1A $\square$ |  | 15 | $\square V_{C C}$ |
| S0 $\square$ | 3 | 14 | $\square 1 \mathrm{Y}$ |
| 1DE $\square$ | 4 | 13 | $\square 1 \mathrm{Z}$ |
| S1 $\square$ | 5 | 12 | 2DE |
| 2A $\square$ | 6 | 11 | 1 2Z |
| 2B $\square$ | 7 | 10 | $\square 2 \mathrm{Y}$ |
| GND ■ | 8 | 9 | GND |

Circuit Function Table

| INPUTS ${ }^{(1)}$ |  |  |  |  |  | OUTPUTS ${ }^{(1)}$ |  | LOGIC DIAGRAM |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $1 \mathrm{~V}_{\text {ID }}$ | $2 \mathrm{~V}_{\text {ID }}$ | S1 | S0 | 1DE | 2DE | $1 \mathrm{~V}_{\text {OD }}$ | $2 \mathrm{~V}_{\text {OD }}$ |  |
| X | X | X | X | L | L | Z | Z |  |
| $>100 \mathrm{mV}$ | X | L | L | H | L | H | Z |  |
| $<-100 \mathrm{mV}$ | X | L | L | H | L | L | Z |  |
| $<-100 \mathrm{mV}$ | X | L | L | H | H | L | L |  |
| $>100 \mathrm{mV}$ | X | L | L | H | H | H | H |  |
| $>100 \mathrm{mV}$ | X | L | L | L | H | Z | H |  |
| $<-100 \mathrm{mV}$ | X | L | L | L | H | Z | L |  |
| $>100 \mathrm{mV}$ | X | H | L | H | L | H | Z |  |
| <-100 mV | X | H | L | H | L | L | Z |  |
| $<-100 \mathrm{mV}$ | <-100 mV | H | L | H | H | L | L |  |
| <-100 mV | $>100 \mathrm{mV}$ | H | L | H | H | L | H |  |
| $>100 \mathrm{mV}$ | $<-100 \mathrm{mV}$ | H | L | H | H | H | L |  |
| $>100 \mathrm{mV}$ | $>100 \mathrm{mV}$ | H | L | H | H | H | H |  |
| X | > 100 mV | H | L | L | H | Z | H |  |
| X | $<-100 \mathrm{mV}$ | H | L | L | H | Z | L |  |
| X | $>100 \mathrm{mV}$ | L | H | H | L | H | Z |  |
| X | $<-100 \mathrm{mV}$ | L | H | H | L | L | Z |  |
| X | $<-100 \mathrm{mV}$ | L | H | H | H | L | L |  |
| X | $>100 \mathrm{mV}$ | L | H | H | H | H | H |  |
| X | $>100 \mathrm{mV}$ | L | H | L | H | Z | H |  |
| X | $<-100 \mathrm{mV}$ | L | H | L | H | Z | L |  |
| X | > 100 mV | H | H | H | L | H | Z |  |
| X | $<-100 \mathrm{mV}$ | H | H | H | L | L | Z |  |
| <-100 mV | $<-100 \mathrm{mV}$ | H | H | H | H | L | L |  |
| $<-100 \mathrm{mV}$ | $>100 \mathrm{mV}$ | H | H | H | H | H | L |  |
| $>100 \mathrm{mV}$ | $<-100 \mathrm{mV}$ | H | H | H | H | L | H |  |
| $>100 \mathrm{mV}$ | $>100 \mathrm{mV}$ | H | H | H | H | H | H |  |
| $>100 \mathrm{mV}$ | X | H | H | L | H | Z | H |  |
| $<-100 \mathrm{mV}$ | X | H | H | L | H | Z | L |  |

(1) $\mathrm{H}=$ high level, $\mathrm{L}=$ low level, $\mathrm{Z}=$ high impedance, $\mathrm{X}=$ don't care

## PARAMETER MEASUREMENT INFORMATION



Figure 1. Voltage and Current Definitions


Figure 2. Differential Output Voltage ( $\mathrm{V}_{\mathrm{OD}}$ ) Test Circuit


NOTE: All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 0.25$ ns, pulse repetition rate (PRR) $=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} ; \mathrm{R}_{\mathrm{L}}=100 \Omega ; \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.; the measurement of $\mathrm{V}_{\mathrm{OC}(\mathrm{PP})}$ is made on test equipment with a $-3-\mathrm{dB}$ bandwidth of at least 300 MHz .

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage


NOTE: All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 0.25 \mathrm{~ns}$, pulse repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 4. Timing Test Circuit and Waveforms

PARAMETER MEASUREMENT INFORMATION (continued)


NOTE: All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 1 \mathrm{~ns}$, pulse repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions


Figure 6. Example Switch, Setup, and Hold Times

PARAMETER MEASUREMENT INFORMATION (continued)
$t_{(S E T)}$ and $t_{(H O L D)}$ times specify that data must be in a stable state before and after multiplex control switches.
Table 1. Receiver Input Voltage Threshold Test

| APPLIED <br> VOLTAGES |  | RESULTING DIFFERENTIAL <br> INPUT VOLTAGE | RESULTING COMMON- <br> MODE INPUT VOLTAGE | OUTPUT ${ }^{(1)}$ |
| :---: | :---: | :---: | :---: | :---: |
| $\mathbf{V}_{\mathbf{I A}}$ | $\mathbf{V}_{\text {IB }}$ | $\mathbf{V}_{\text {ID }}$ | $\mathbf{V}_{\mathbf{I C}}$ |  |
| 1.25 V | 1.15 V | 100 mV | 1.2 V | H |
| 1.15 V | 1.25 V | -100 mV | 1.2 V | L |
| 4.0 V | 3.9 V | 100 mV | 3.95 V | H |
| 3.9 V | 4.0 V | -100 mV | 3.95 V | L |
| 0.1 V | 0.0 V | 100 mV | 0.05 V | H |
| 0.0 V | 0.1 V | -100 mV | 0.05 V | L |
| 1.7 V | 0.7 V | 1000 mV | 1.2 V | H |
| 0.7 V | 1.7 V | -1000 mV | 1.2 V | L |
| 4.0 V | 3.0 V | 1000 mV | 3.5 V | H |
| 3.0 V | 4.0 V | -1000 mV | 3.5 V | L |
| 1.0 V | 0.0 V | 1000 mV | 0.5 V | H |
| 0.0 V | 1.0 V | -1000 mV | 0.5 V | L |

(1) $H=$ high level, $L=$ low level

## EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

INPUT LVDS122


OUTPUT LVDS122


## TYPICAL CHARACTERISTICS



Figure 7.
PEAK-TO-PEAK JITTER
FREQUENCY


Figure 10.


Figure 13.


COMMON-MODE INPUT VOLTAGE


Figure 8.
PEAK-TO-PEAK JITTER
DATA RATE


Figure 11.


Figure 14.

DIFFERENTIAL PROPAGATION
DELAY
VS
TEMPERATURE


Figure 9.
PEAK-TO-PEAK JITTER
FREQUENCY


Figure 12.


Figure 15.

## TYPICAL CHARACTERISTICS (continued)



Figure 16.


Horizontal Scale= $\mathbf{2 0 0}$ ps/div
LVPECL-to-LVDS
Figure 18.


Figure 17.
LVDS122
1.5 Gbps, $2^{23}-1$ PRBS


Horizontal Scale= $\mathbf{1 0 0}$ ps/div LVPECL-to-LVDS

Figure 19.

TYPICAL CHARACTERISTICS (continued)

LVDS122
622 Mbps, $2^{\mathbf{2 3}} \mathbf{- 1} 1$ PRBS


Horizontal Scale= $\mathbf{2 0 0}$ ps/div LVDS-to-LVDS

Figure 20.

LVDS122
1.5 Gbps, $\mathbf{2}^{23}-1$ PRBS


Horizontal Scale= $100 \mathrm{ps} /$ div LVDS-to-LVDS

Figure 21.


Figure 22. Jitter Setup Connections for SN65LVDS122

## APPLICATION INFORMATION

TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)


Figure 23. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)


Figure 24. Current-Mode Logic (CML)


Figure 25. Single-Ended (LVPECL)


Figure 26. Low-Voltage Differential Signaling (LVDS)

## PACKAGING INFORMATION

| Orderable Device | Status ${ }^{(1)}$ | Package Type | Package Drawing | Pins | Package Qty | $\text { Eco Plan }{ }^{(2)}$ | Lead/Ball Finish | MSL Peak Temp ${ }^{(3)}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS122D | ACTIVE | SOIC | D | 16 | 40 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122DG4 | ACTIVE | SOIC | D | 16 | 40 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122DR | ACTIVE | SOIC | D | 16 | 2500 | $\begin{gathered} \hline \text { Green (RoHS \& } \\ \text { no } \mathrm{Sb} / \mathrm{Br}) \\ \hline \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122DRG4 | ACTIVE | SOIC | D | 16 | 2500 | $\begin{gathered} \text { Green (RoHS \& } \\ \text { no } \mathrm{Sb} / \mathrm{Br}) \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122PW | ACTIVE | TSSOP | PW | 16 | 90 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122PWG4 | ACTIVE | TSSOP | PW | 16 | 90 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122PWR | ACTIVE | TSSOP | PW | 16 | 2000 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDS122PWRG4 | ACTIVE | TSSOP | PW | 16 | 2000 | $\begin{gathered} \text { Green (RoHS \& } \\ \text { no Sb/Br) } \\ \hline \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122D | ACTIVE | SOIC | D | 16 | 40 | $\begin{gathered} \text { Green (RoHS \& } \\ \text { no Sb/Br) } \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122DG4 | ACTIVE | SOIC | D | 16 | 40 | $\begin{gathered} \hline \text { Green (RoHS \& } \\ \text { no } \mathrm{Sb} / \mathrm{Br}) \\ \hline \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122DR | ACTIVE | SOIC | D | 16 | 2500 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122DRG4 | ACTIVE | SOIC | D | 16 | 2500 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122PW | ACTIVE | TSSOP | PW | 16 | 90 | $\begin{gathered} \text { Green (RoHS \& } \\ \text { no Sb/Br) } \\ \hline \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122PWG4 | ACTIVE | TSSOP | PW | 16 | 90 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122PWR | ACTIVE | TSSOP | PW | 16 | 2000 | $\begin{gathered} \text { Green (RoHS \& } \\ \text { no Sb/Br) } \\ \hline \end{gathered}$ | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVDT122PWRG4 | ACTIVE | TSSOP | PW | 16 | 2000 | Green (RoHS \& no $\mathrm{Sb} / \mathrm{Br}$ ) | CU NIPDAU | Level-1-260C-UNLIM |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
${ }^{(2)}$ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS \& no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb -Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb -Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS \& no $\mathbf{S b} / \mathrm{Br}$ ): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine ( Br ) and Antimony (Sb) based flame retardants ( Br or Sb do not exceed $0.1 \%$ by weight in homogeneous material)
${ }^{(3)}$ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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## TAPE AND REEL INFORMATION


*All dimensions are nominal

| Device | Package <br> Type | Package <br> Drawing | Pins | SPQ | Reel <br> Diameter <br> $(\mathbf{m m})$ | Reel <br> Width <br> $\mathbf{W 1}(\mathbf{m m})$ | $\mathbf{A 0}(\mathbf{m m})$ | B0 $(\mathbf{m m})$ | K0 $(\mathbf{m m})$ | P1 <br> $(\mathbf{m m})$ | W <br> $(\mathbf{m m})$ | Pin1 <br> Quadrant |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS122DR | SOIC | D | 16 | 2500 | 330.0 | 16.4 | 6.5 | 10.3 | 2.1 | 8.0 | 16.0 | Q1 |
| SN65LVDS122PWR | TSSOP | PW | 16 | 2000 | 330.0 | 12.4 | 6.67 | 5.4 | 1.6 | 8.0 | 12.0 | Q1 |
| SN65LVDT122DR | SOIC | D | 16 | 2500 | 330.0 | 16.4 | 6.5 | 10.3 | 2.1 | 8.0 | 16.0 | Q1 |
| SN65LVDT122PWR | TSSOP | PW | 16 | 2000 | 330.0 | 12.4 | 6.67 | 5.4 | 1.6 | 8.0 | 12.0 | Q1 |


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS122DR | SOIC | D | 16 | 2500 | 346.0 | 346.0 | 33.0 |
| SN65LVDS122PWR | TSSOP | PW | 16 | 2000 | 346.0 | 346.0 | 29.0 |
| SN65LVDT122DR | SOIC | D | 16 | 2500 | 346.0 | 346.0 | 33.0 |
| SN65LVDT122PWR | TSSOP | PW | 16 | 2000 | 346.0 | 346.0 | 29.0 |



| PIMS $^{* *}$ | $\mathbf{8}$ | $\mathbf{1 4}$ | $\mathbf{1 6}$ | $\mathbf{2 0}$ | $\mathbf{2 4}$ | $\mathbf{2 8}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A MAX | 3,10 | 5,10 | 5,10 | 6,60 | 7,90 | 9,80 |
| A MIN | 2,90 | 4,90 | 4,90 | 6,40 | 7,70 | 9,60 |

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15 .
D. Falls within JEDEC MO-153

D (R-PDSO-G16)
PLASTIC SMALL-OUTLINE PACKAGE


NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.

C Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006(0,15)$ per end.
D Body width does not include interlead flash. Interlead flash shall not exceed $.017(0,43)$ per side.
E. Reference JEDEC MS-012 variation AC.

## D(R-PDSO-G16)



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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